

SLD104AU

AIGaAs Laser Diode

Description

The SLD104AU is a AlGaAs laser diode developed for positive power supplies. In comparison with the SLD104U, this device attains even lower power consumption levels.

Features

- Low power consumption
- Single power supply
- Low noise
- Microminiaturized package (\u00e95.6mm)

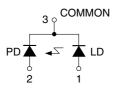
Structure

- AlGaAs double hetero-type laser diode
- PIN photo diode for laser optical power output monitor

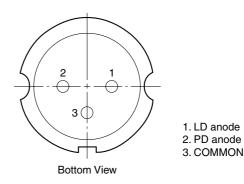
Absolute Maximum Ratings (Tc = 25°C)

 Optical power output 	Pomax		5	mW
 Reverse voltage 	VR	LD	2	V
		PD	15	V
• Operating temperature	Тор	r	-10 to +60	°C
Storage temperature	Tstg	l	-40 to +85	°C

Connection Diagram



Pin Configuration



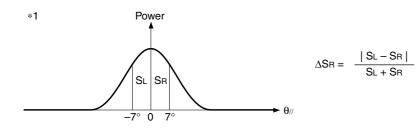
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Electrical and Optical Characteristics (Tc = 25°C)

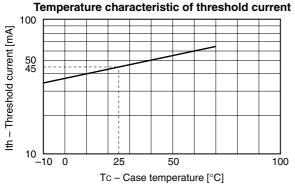
Tc: Case temperature

Iter	n	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshold current		lth			45	60	mA
Operating current		lop	Po = 3mW		52	70	mA
Operating voltage		Vop	Po = 3mW	1.7	1.9	2.5	V
Wavelength		λ	Po = 3mW	760	780	800	nm
Monitor current		Im	Po = 3mW, V _R = 5V	0.08	0.15	0.4	mA
	Perpendicular	θ⊥	Po = 3mW	20	32	45	degree
Radiation angle (F. W. H. M.*)	Parallel	θ//		9	17	25	degree
(,	Asymmetry	$\Delta SR *1$				20	%
Positional	Position	$\Delta X, \Delta Y, \Delta Z$	Po = 3mW			±150	μm
accuracy	Angle	$\Delta \phi \bot$	1 0 - 01111			±3	degree
Differential efficiency		ησ	Po = 3mW	0.2	0.45	0.7	mW/mA
Astigmatism		As	Po = 3mW Z// – Z⊥			15	μm
Signal to noise ratio		S/N	fc = 7.5MHz ∆f = 30kHz Po = 4mW		88		dB
Dark current of PD		lD	VR = 5V			150	nA
Capacitance of PD		С⊤	VR = 5V, f = 1MHz			30	pF

* F. W. H. M. : Full Width at Half Maximum



Example of Representative Characteristics



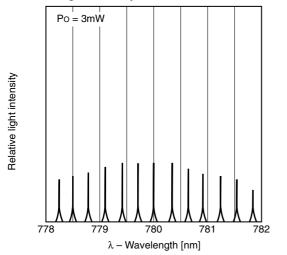
Radiant intensity (optional scale) θ 0 -40 0 -20 Angle [degree]

1.0

0.5

PIN diode current-voltage characteristics 0.25 [mA] 14 $Tc = 25^{\circ}C$ Po = 3mW v -1.0 1.0 [V] 0 -0.25

Relative light intensity vs. Waveform characteristics



Optical power output vs. Forward current characteristics

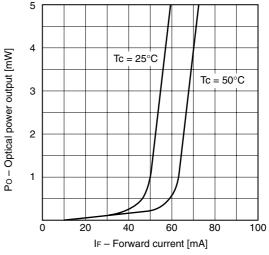
Far field pattern (FFP)

Po = 3mW

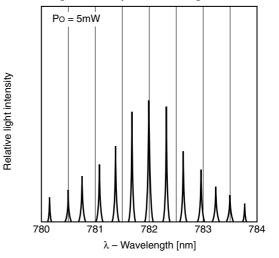
 θ_{\perp}

20

40



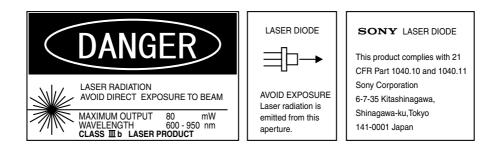
Relative light intensity vs. Wavelength characteristics



Notes on Operation

Care should be taken for the following points when using this product.

(1) This product corresponds to a Class 3B product under IEC60825-1 and JIS standard C6802 "Laser Product Emission Safety Standards".



(2) Eye protection against laser beams

Take care not to allow laser beams to enter your eyes under any circumstances.

For observing laser beams, ALWAYS use safety goggles that block laser beams. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.

(3) Gallium Arsenide

This product uses gallium arsenide (GaAs). This is not a problem for normal use, but GaAs vapors may be potentially hazardous to the human body. Therefore, never crush, heat to the maximum storage temperature or higher, or place the product in your mouth.

In addition, the following disposal methods are recommended when disposing of this product.

- 1. Engaging the services of a contractor certified in the collection, transport and intermediate treatment of items containing arsenic.
- 2. Managing the product through to final disposal as specially managed industrial waste which is handled separately from general industrial waste and household waste.

(4) Prevention of surge current and electrostatic discharge

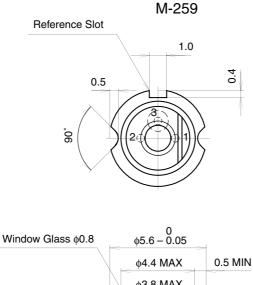
Laser diodes are most sensitive to electrostatic discharge among semiconductors. When a large current is passed through the laser diode for even an extremely short time, the strong light emitted from the laser diode promotes deterioration and then destruction of the laser diode. Therefore, note that surge current should not flow to the laser diode driving circuit from switches and others. Also, if the laser diode is handled carelessly, it may be destroyed instantly because electrostatic discharge is easily applied by a human body. Therefore, be extremely careful about overcurrent and electrostatic discharge.

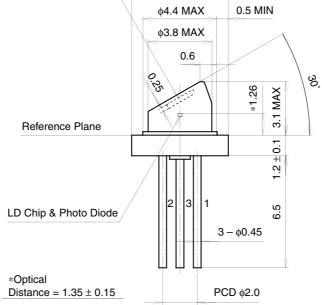
(5) Use for special applications

This product is not designed or manufactured for use in equipment used under circumstances where failure may pose a risk to life and limb, or result in significant material damage, etc.

Consult your Sony sales representative when investigating use for medical, vehicle, nuclear power control or other special applications. Also, use the power supply that was designed not to exceed the optical power output specified at the absolute maximum ratings.

Package Outline Unit: mm





SONY CODE	M-259		
EIAJ CODE			
JEDEC CODE		PACKAGE MASS	0.3g